



CEPC Vertex Detector R&D Status

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Outline

- CEPC Vertex detector
- Pixel prototype JadePix1
- Summary and outlook

Requirement of CEPC Vertex Detector

- The identification of heavy-flavor (b/c) quarks and tau-leptons is essential for CEPC physics program.
- Precision measurement of H→bb, cc requires track parameter resolution

$$\sigma(r\phi) = a \oplus \frac{b}{p(\text{GeV})\sin^{3/2}\theta} \ \mu\text{m}$$

- a: intrinsic resolution of vertex
- b: multiple scattering effect
- a=5, b=10 taken as design value

Performance goals for Vertex Detector

- Spatial resolution near the IP $\sigma_{SP} \leq 3\mu m$ (high granularity, small pixel size)
- Material budget ≤ 0.15% X₀/layer (monolithic pixel sensor thick 50µm + air cooling power consumption 50mW/cm²)
- Low detector occupancy < 0.5% (high granularity and/or short readout time)
- Radiation tolerance:

~1MRad/y(TID) and 10¹³ 1MeV $n_{eq}/cm^2/y(NIEL)$

Sensor Options

- No sensor technology satisfies all the requirements of CEPC vertex detector (yet)
- Potential options after extensive R&D
 - Depleted Field Effect Transitor (DEPFET) Belle-II vertex
 - CMOS Pixel Sensors (CPS) ALICE ITS , STAR PXL, JadePix1 (this talk), JadePix2 (see talk by Y. Zhou)
 - Silicon-on-insulator (SOI)
 Explored at IHEP (see talk by Y. Zhou)

CMOS Pixel Sensor – TowerJazz Process

 Integrated pixel sensor and readout electronics on the same silicon bulk with the industry "standard" CMOS process

-> Low material budget, low power consumption, low cost ...



- TowerJazz CIS 0.18µm process features:
 - Quadruple well process: deep P-Well shields N-Well of PMOS transistors, allowing for full CMOS circuitry within the active area
 - Feature size of 0.18um and 6 metal layers: high-density and low power
 - Thin gate oxide (3nm): radiation tolerance
 - Thick (> 20µm) and high resistivity (1kΩ·cm) epitaxial layer: possible improvement of charge collection

Sensor Design & TCAD Simulation

 Y. Zhang, M. Zhao
 Charge collection performance with different sensor diode geometries, epitaxial-layer properties and radiation damages evaluated with TCAD simulation



Readout Electronics

Y. Zhang, Y. Zhou, Y. Lu

- Conventional (simple and robust) 2T/3T in-pixel readout electronics, AC coupling structure with biased voltage up to 10V Enlarged depleted region/electric field -> potential improvement in charge collection
- Analog signal readout with the robust rolling shutter scheme



In-pixel readout structures

Peripheral circuitry

First Submission - JadePix1

- Joint MPW submission with IPHC in November 2015
- Aimed to understand charge collection performance with different diode geometries, epitaxial-layer properties, and potential radiation tolerance
- Diced samples returned to IHEP in June 2016
- Got name "JadePix1" on 29 December 2017 by voting.





Diced pixel sensor

JadePix1 Test System

• Test system developed to characterize JadePix1 at IHEP





Test System Hardware Design

K. Wang, N. Wang, J. Tao

- FPGA board : control, data handle, data transmission
 - Xilinx KC705 FPGA board with mature technology
 - Data transmission with PCIe, close to 6Gbps
 - Main readout function of firmware :
 - Control CMOS sensor: initialize, address selection, clock
 - Control ADC sampling, serial data read
 - Data conversion: from serial to parallel, transmit to downstream
- Mother board: low noise stable power supply, AD conversion
 - Use 16 bit ADC , high resolution; support 8Vpp differential input, large dynamical range
 - Maximum support 16 ADC simultaneous readout
 - Provide low noise power supply and many types of bias voltage, support all matrix readout from sensor
- Daughter board : Good shield with strong anti-interference ability
 - Signal amplification with low noise
 - Standalone front-end suitable for radiation test



FPGA Firmware

- Xilinx Kintex-7 FPGA
- Receive 16bit ADC 2MHz clock / control PC

R. Kiuchi, J. Tao





FPGA Firmware Development





(1536 bytes + 48*(4+4)bytes = 1920 bytes) **Row header** + **Row data** + **Row footer** +

\Event data\

(1920 *16 bit)

1 Event : 1928 bytes

Define data structure for each pixel

matrix frame, with header and footer

Data structure



\Event header\

\0xaaaa aaaa\

(32 bit = 4 bytes)

pixel(16 bit = 2 bytes)

46 f6 69 f3 24 eb b5 f5

4c f5 ba f5 06 fe 53 f8

03 00 2f e0 03 0f 38 f8

85 f4 27 f6 30 f2 37 f7

59 f2 16 f7 65 f1 bc ed

c2 fb 43 f2 44 f0 5c f3

e4 f6 63 f8 01 f3 1a f3

cd f5 79 f9 43 ff 4e fd 03 00 2f e0 2f 0f f8 fa

92 f6 f0 f4 e2 f5 e1 f5

R. Kiuchi, T. Yang



48th row header / footer

\Event footer\

03 00 2f e0 02 0f 28 f8

2b f0 c1 f6 92 f2 72 f1

63 f3 48 f3 77 f3 45 e8

50 f7 38 f3 8e f5 a3 f5

d1 f5 b0 f6 56 00 aa f0

13 f2 85 f6 c1 f5 85 f3

03 00 2f e0 2e 0f e8 fa

d0 f1 fd ec 85 f1 c9 f2

52 f7 d9 f1 f8 f0 2d eb

2e f4 a2 f4 37 f5 a2 f6

03 00 2f e0 f0 f0 f0 f0

1st row header / footer

aa aa aa aa 00 0f 08 f8 dc eb 7b ed d5 ea 6d eb

cc ef b3 ee 52 ec c3 eb 8b eb 31 e9 70 f8 9f eb

03 ef f1 e7 a5 e8 5c e8 03 00 2f e0 01 0f 18 f8

84 f0 6e ed b9 f6 50 f2 d6 f1 a8 f0 84 f1 fb fb

d6 f4 a7 f0 83 01 a5 ee 47 ef 43 f1 98 f6 78 ea

39 fa ac f9 4e ef 9c ea 03 00 2f e0 2d 0f d8 fa

eb f4 58 f2 94 fe fa f3 59 f6 ee ef e2 f4 68 ed

e3 f5 e2 f1 8a ff bf f4 a9 f2 50 f4 1f ee 48 eb

event footer

\0xf0f0 f0f0f0\

event header

00000750

00000760

00000770

00000780

(32 bit = 4 bytes)

15

....R....1.p...

l . . n . . . P

....x.

../...(.F.i.\$...

+....s.

c.H.w.E.../...8.

P.8.....'.0.7.

....V...Y...e...

9...N..../.-...

|....C.D.\.

|..X...Y....h.

|../....c.... |....y.C.N.

R......./././...

. . . . 7

|....H.

|../....|

Noise Level (Preliminary)

 Scan A1-A10 pixel matrix (33µm, 16x48), Correlated Double Sampling (CDS), subtract adjacent frame to suppress noise.



L. Chen , H. Zhu

⁵⁵ Fe Radiation test (Preliminary)

L. Chen, H. Zhu, R. Kiuchi

• Use ⁵⁵ Fe for pixel gain calibration



- $k_{\alpha}k_{\beta}$ peak can be recognized clearly

Electrode Size (Preliminary)

L. Chen , H. Zhu

 Larger electrode size -> better charge collection, but larger capacitance, low gain and higher noise



Optimization: Q/C (analog power consumption), S/N (spatial resolution)

⁹⁰Sr Radiation test (Preliminary)

L. Chen , H. Zhu

• Use ⁹⁰ Sr to measure the charge collection efficiency for MIP



- Cluster with Landau distribution, use MPV for CCE calculation
- Uncertain of radiation angle, will use electron beam for better CCE
- Optimization: Q/C (analog power consumption), S/N (spatial resolution)

Irradiation with neutron

- Three batches of neutron irradiation with Xi'an pulse reactor : 10¹², 5x10¹², 10¹³.
- Build TCAD simulation with radiation damage model



DESY test beam

- Reserved DESY test beam (Aug. 27- Sep. 2, 2018), characterize pixel special resolution and detector efficiency.
- Preparing: new firmware, EUDAQ plugin, offline reconstruction software, etc.



Summary and outlook

- To fulfill the CEPC physics program, the Vertex detector has to be built with high resolution, low material budget and radiation hard.
- The first pixel prototype JadePix1 has been built and tested with radiation sources.
- Test beam will be carried out in August for spatial resolution and detector efficiency characterization.